



## E. Compound Semiconductors 분과

2021년 1월 29일(금), 09:00-10:30 / 채널 C

### [FC1-E] Compound Semiconductors III

좌장: 민병규 박사 (ETRI)

<p><b>FC1-E-1</b> 09:00-09:15</p>	<p><b>SiC 파워 모듈 적용을 위한 고방열 나노/마이크론급 Cu Sintering Paste 무가압 접합</b> 배현철<sup>1,2</sup>, 오애선<sup>1</sup>, 백범규<sup>3</sup>, 박웅비<sup>3</sup>, 최소영<sup>4</sup>, 김영훈<sup>4</sup> <sup>1</sup>한국전자통신연구원 DMC융합연구단 국방전력/센서모듈연구실, <sup>2</sup>과학기술연합대학원대학교 ETRIS쿨 차세대소자공학과, <sup>3</sup>(주)경동엠텍, <sup>4</sup>(주)제엠제코</p>
<p><b>FC1-E-2</b> 09:15-09:30</p>	<p><b>Effect of GaAs Buffer Thickness on InAs Quantum Dots Epitaxially Grown on Si Substrate</b> Yeonhwa Kim<sup>1,2</sup>, Seungwan Woo<sup>3</sup>, Rafael Chu<sup>1,2</sup>, Geunhwan Ryu<sup>1</sup>, Jae-Hoon Han<sup>1</sup>, In-Hwan Lee<sup>3</sup>, Won Jun Choi<sup>1</sup>, and Daehwan Jung<sup>1,2</sup> <sup>1</sup>Center for Opto-electronic Materials and Devices, KIST, <sup>2</sup>Division of Nano and Information Technology, KIST School at UST, <sup>3</sup>Department of Materials Science and Engineering, Korea University</p>
<p><b>FC1-E-3</b> 09:30-09:45</p>	<p>철회</p>
<p><b>FC1-E-4</b> 09:45-10:00</p>	<p><b>Phase Change Characteristics and Stable Device Behavior Caused by Carbon Bonding with Ge and Sb in Ge<sub>2</sub>Sb<sub>2</sub>Te<sub>5</sub></b> Jeong Hwa Han<sup>1</sup>, Hun Jeong<sup>1</sup>, Han Jin Park<sup>2</sup>, Young-Kyun Kwon<sup>2</sup>, and Mann-HoCho<sup>1</sup> <sup>1</sup>Department of Physics, College of Natural Science, Yonsei University, <sup>2</sup>Department of Physics and Research Institute for Basic Sciences, Kyung Hee University</p>
<p><b>FC1-E-5</b> 10:00-10:15</p>	<p><b>고방열 DBC/AMB기판 및 고열전도 접합 소재를 이용한 SiC 파워 모듈의 열 해석</b> 김동환<sup>1,2</sup>, 오애선<sup>1</sup>, 안현식<sup>1</sup>, 박은영<sup>1</sup>, 김경현<sup>1</sup>, 전성재<sup>3</sup>, 배현철<sup>1,2</sup> <sup>1</sup>한국전자통신연구원 DMC융합연구단 국방전력/센서모듈연구실, <sup>2</sup>과학기술연합대학원대학교 차세대소자공학과, <sup>3</sup>한국기계연구원 나노융합장비연구부 나노역학장비연구실</p>
<p><b>FC1-E-6</b> 10:15-10:30</p>	<p><b>Cumulative Effect on the Degradation of AlGaIn/GaN HEMTs by Proton Irradiation</b> Dong-Seok Kim<sup>1</sup>, Young Jun Yoon<sup>1</sup>, Jae Sang Lee<sup>1</sup>, Jeong-Gil Kim<sup>2</sup>, and Jung-Hee Lee<sup>2</sup> <sup>1</sup>Korea Multi-Purpose Accelerator Complex, KAERI, <sup>2</sup>School of Electronic and Electrical Engineering, Kyungpook National University</p>

1월 29일 (금)